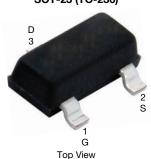


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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

SOT-23 (TO-236)



Marking code: 9K

| PRODUCT SUMMARY | | | | | |
|---|--------|--|--|--|--|
| V _{DS} (V) | 40 | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$ | 0.0265 | | | | |
| $R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$ | 0.032 | | | | |
| I _D (A) | 8 | | | | |
| Configuration | Single | | | | |
| Package | SOT-23 | | | | |

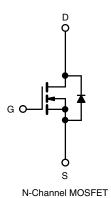
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



| PARAMETER | | SYMBOL | LIMIT | UNIT | |
|---|-------------------------|-----------------------------------|-------------|------|--|
| Drain-source voltage | | V _{DS} | 40 | .,, | |
| Gate-source voltage | V _{GS} | ± 20 | V | | |
| Continuous drain current | T _C = 25 °C | | 8 | | |
| | T _C = 125 °C | I _D | 4.8 | | |
| Continuous source current (diode conduct | Is | 2.7 | Α | | |
| Pulsed drain current ^a | I _{DM} | 32 | | | |
| Single pulse avalanche current | L = 0.1 mH | I _{AS} | 8.5 | | |
| Single pulse avalanche energy | L = U.T IIII | E _{AS} | 3.6 | mJ | |
| Maniero na consultacionette a 9 | T _C = 25 °C | D | 3 | W | |
| Maximum power dissipation ^a | T _C = 125 °C | P_{D} | 1 | VV | |
| Operating junction and storage temperatur | e range | T _J , T _{stg} | -55 to +175 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|----------------------------|------------------------|------------|-------|------|--|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | | |
| Junction-to-ambient | PCB Mount ^b | R_{thJA} | 166 | °C/W | | |
| Junction-to-foot (drain) | | R_{thJF} | 50 |] | | |

Notes

- a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)



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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT | |
|---|---------------------|--|--|------|-------|--------|------|--|
| Static | | | | | | | | |
| Drain-source breakdown voltage | V _{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | | 40 | - | - | V | |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | | 1.5 | 2.0 | 2.5 | \ \ | |
| Gate-source leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | - | - | ± 100 | nA | |
| | | $V_{GS} = 0 V$ | V _{DS} = 40 V | - | - | 1 | | |
| Zero gate voltage drain current | I _{DSS} | $V_{GS} = 0 V$ | $V_{DS} = 40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$ | - | - | 50 | μΑ | |
| | | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 175 °C | - | - | 150 | | |
| On-state drain current a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 V$ | 10 | - | - | Α | |
| | | V _{GS} = 10 V | I _D = 4 A | - | 0.021 | 0.0263 | Ω | |
| Drain agures on state registence 8 | Б | V _{GS} = 10 V | I _D = 4 A, T _J = 125 °C | - | - | 0.039 | | |
| Drain-source on-state resistance ^a | R _{DS(on)} | V _{GS} = 10 V | I _D = 4 A, T _J = 175 °C | - | - | 0.044 | | |
| | | V _{GS} = 4.5 V | I _D = 3 A | - | 0.025 | 0.032 | | |
| Forward transconductance b | 9 _{fs} | $V_{DS} = 15 \text{ V}, I_D = 5 \text{ A}$ | | - | 21 | - | S | |
| Dynamic ^b | | | | | | | | |
| Input capacitance | C _{iss} | | | - | 358 | 500 | pF | |
| Output capacitance | C _{oss} | $V_{GS} = 0 V$ | $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$ | - | 135 | 190 | | |
| Reverse transfer capacitance | C _{rss} | | | - | 17 | 24 | | |
| Total gate charge ^c | Qg | | | - | 6.7 | 9.4 | | |
| Gate-source charge ^c | Q _{gs} | V _{GS} = 10 V | $V_{DS} = 20 \text{ V}, I_{D} = 3 \text{ A}$ | - | 1.4 | - | nC | |
| Gate-drain charge ^c | Q_{gd} | | | - | 1.1 | - | | |
| Gate resistance | R _g | f = 1 MHz | | 2.8 | 7.1 | 11.3 | Ω | |
| Turn-on delay time ^c | t _{d(on)} | $V_{DD} = 20 \text{ V, } R_L = 13.3 \Omega,$ $I_D \cong 1.5 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$ | | - | 7.8 | 11 | - ns | |
| Rise time ^c | t _r | | | - | 3.7 | 5.2 | | |
| Turn-off delay time ^c | t _{d(off)} | | | - | 15.6 | 22 | | |
| Fall time ^c | t _f | | | - | 2.9 | 4.0 | | |
| Source-Drain Diode Ratings and Char | acteristics b | | | | | | | |
| Pulsed current ^a | I _{SM} | | | - | - | 11 | Α | |
| | | I _F = 5 A, V _{GS} = 0 V | | | | | | |

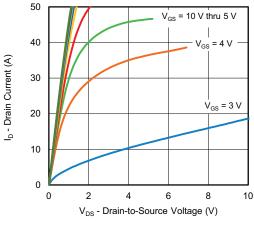
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

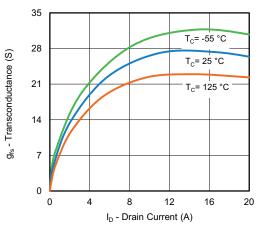
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



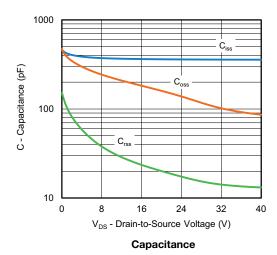
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

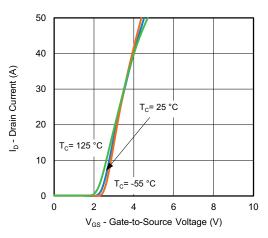


Output Characteristics

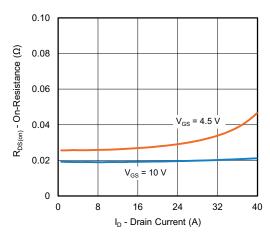


Transconductance

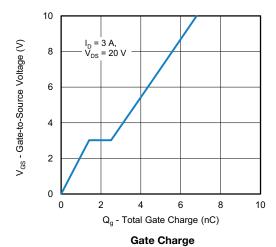




Transfer Characteristics

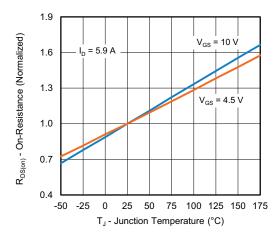


On-Resistance vs. Drain Current

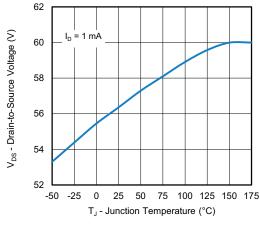




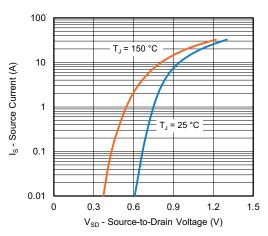
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



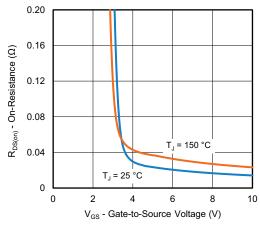
On-Resistance vs. Junction Temperature



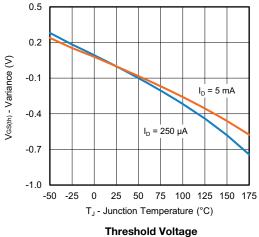
Drain Source Breakdown vs. Junction Temperature



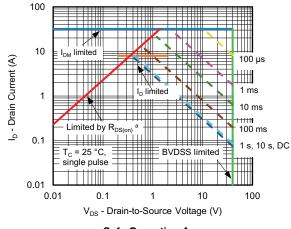
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Tillesilola Voltag



Safe Operating Area

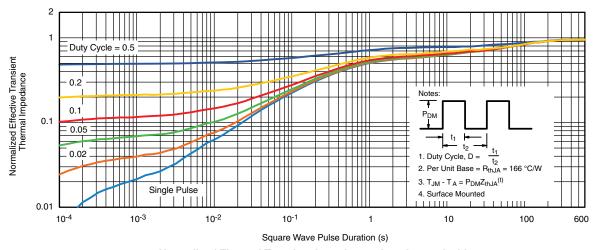
Note

a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

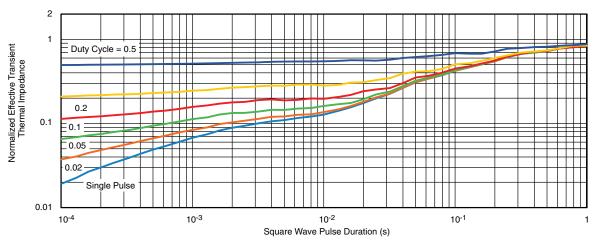
For technical questions, contact: automostechsur



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

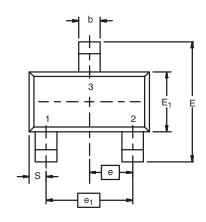
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

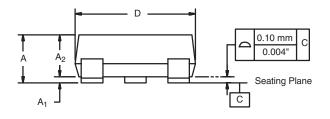
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

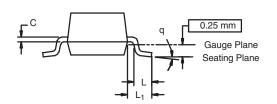
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77410.

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SOT-23 (TO-236): 3-LEAD







| Dim | MILLI | METERS | INCHES | | |
|------------------------|----------|--------|------------|-------|--|
| | Min | Max | Min | Max | |
| Α | 0.89 | 1.12 | 0.035 | 0.044 | |
| A ₁ | 0.01 | 0.10 | 0.0004 | 0.004 | |
| A ₂ | 0.88 | 1.02 | 0.0346 | 0.040 | |
| b | 0.35 | 0.50 | 0.014 | 0.020 | |
| С | 0.085 | 0.18 | 0.003 | 0.007 | |
| D | 2.80 | 3.04 | 0.110 | 0.120 | |
| E | 2.10 | 2.64 | 0.083 | 0.104 | |
| E ₁ | 1.20 | 1.40 | 0.047 | 0.055 | |
| е | 0.95 BSC | | 0.0374 Ref | | |
| e ₁ | 1.90 BSC | | 0.0748 Ref | | |
| L | 0.40 | 0.60 | 0.016 | 0.024 | |
| L ₁ | 0.64 Ref | | 0.025 Ref | | |
| S | 0.50 Ref | | 0.020 Ref | | |
| q | 3° | 8° | 3° | 8° | |
| FCN: S-03946-Rev K 09- | lul-01 | • | | | |

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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